

SMD Schottky Barrier Diode

COMCHIP
www.comchip.com.tw

CDBN0130

$I_o = 100\text{mA}$

$V_R = 30 \text{ Volts}$



Features

Designed for mounting on small surface

Extremely thin package

Low stored charge

Majority carrier conduction

Mechanical data

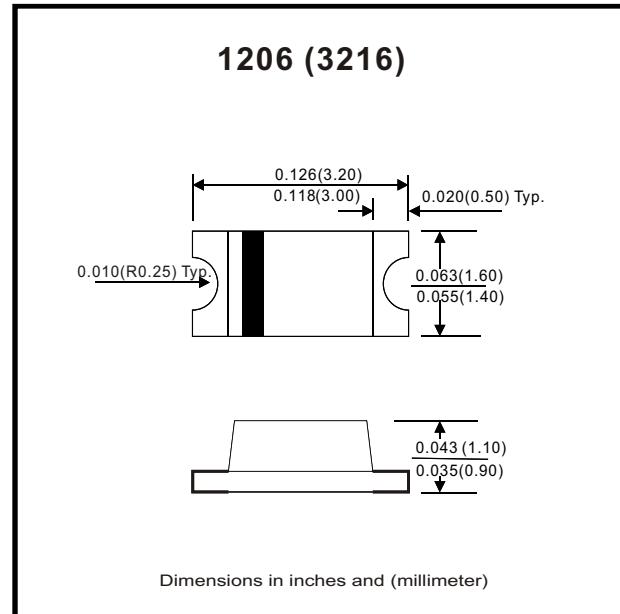
Case: 1206(3216) Standard package, molded plastic

Terminals: Solder plated, solderable per MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any.

Weight: 0.0085 gram.(approximately)



Dimensions in inches and (millimeter)

Maximum Rating (at $T_A = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Conditions | Symbol | Min | Typ | Max | Unit |
|---------------------------------|--|-----------|-----|------|------|------|
| Repetitive peak reverse voltage | | V_{RRM} | | | 35 | V |
| Reverse voltage | | V_R | | | 30 | V |
| Average forward current | | I_o | | | 100 | mA |
| Forward current , surge peak | 8.3 ms single half sine-wave superimposed on rate load(JEDEC method) | I_{FSM} | | 1000 | | mA |
| Power dissipation | | P_D | | | 250 | mW |
| Storage temperature | | T_{STG} | -40 | | +125 | °C |
| Junction temperature | | T_j | -40 | | +125 | °C |

Electrical Characteristics (at $T_A = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Conditions | Symbol | Min | Typ | Max | Unit |
|-------------------------------|--|--------|-----|-----|------|------|
| Forward voltage | $I_F = 100 \text{ mA DC}$ | V_F | | | 0.44 | V |
| Reverse current | $V_R = 30 \text{ V}$ | I_R | | | 30 | uA |
| Capacitance between terminals | $f = 1\text{MHz}$, and 10 VDC reverse voltage | C_T | | 10 | | pF |

RATING AND CHARACTERISTIC CURVES (CDBN0130)

Fig. 1 - Forward characteristics

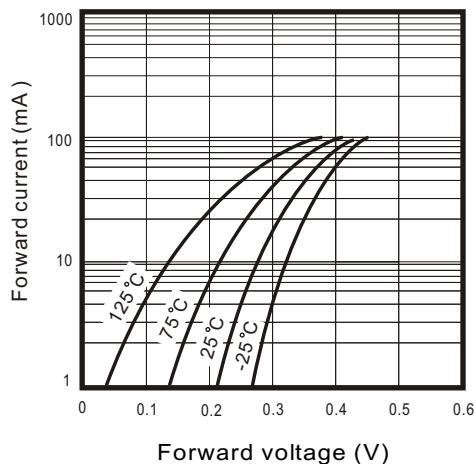


Fig. 2 - Reverse characteristics

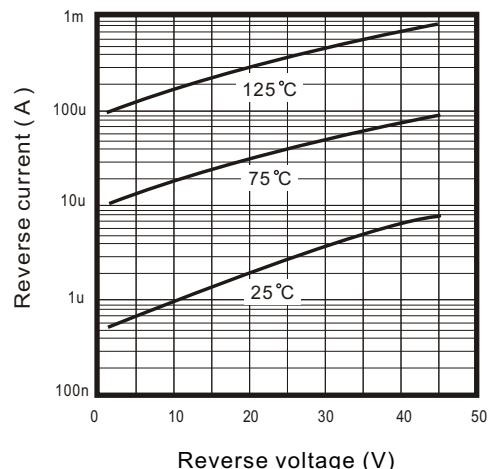


Fig. 3 - Capacitance between terminals characteristics

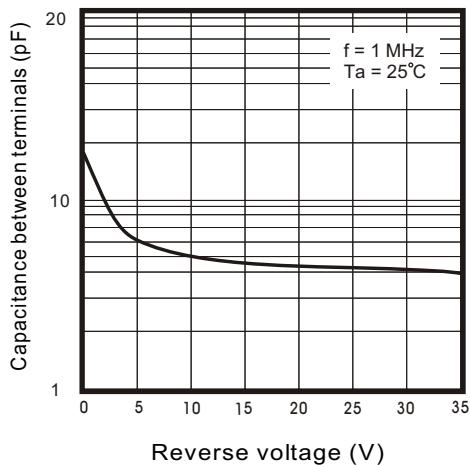


Fig. 4 - Current derating curve

